

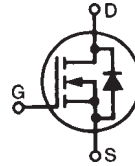
Polar3™ HiperFET™ Power MOSFET

IXFJ26N50P3

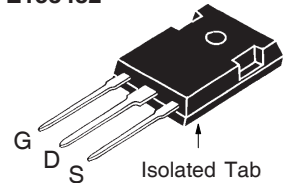
$$\begin{aligned} V_{DSS} &= 500V \\ I_{D25} &= 14A \\ R_{DS(on)} &\leq 265m\Omega \end{aligned}$$

(Electrically Isolated Tab)

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



ISO TO-247™
E153432



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	14	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	78	A
I_A	$T_C = 25^\circ\text{C}$	13	A
E_{AS}	$T_C = 25^\circ\text{C}$	300	mJ
dv/dt	$I_S \leq I_{DM}, V_{DD} \leq V_{DSS}, T_J \leq 150^\circ\text{C}$	35	V/ns
P_D	$T_C = 25^\circ\text{C}$	180	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
F_C	Mounting Torque	1.13 / 10	Nm/lb.in
V_{ISOL}	50/60 Hz, RM, t = 1min	2500	V~
Weight		5	g

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Fast Intrinsic Rectifier
- Avalanche Rated
- Low $R_{DS(ON)}$ and Q_G
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 1mA$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 4mA$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 750 μA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 13A$, Note 1			265 m Ω

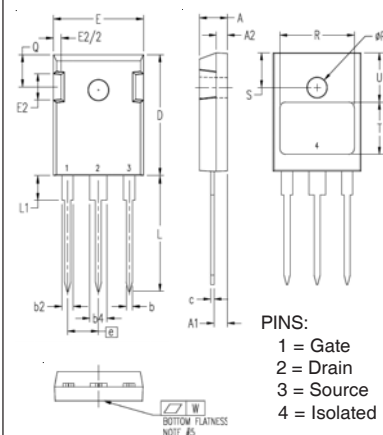
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 13\text{A}$, Note 1	14	23	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		2220	pF
C_{oss}			280	pF
C_{rss}			8	pF
R_{Gi}	Gate Input Resistance		2.1	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 13\text{A}$ $R_G = 3\Omega$ (External)		21	ns
t_r			7	ns
$t_{d(off)}$			38	ns
t_f			5	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 13\text{A}$		42	nC
Q_{gs}			11	nC
Q_{gd}			15	nC
R_{thJC}				0.69°C/W
R_{thCS}		0.30		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			26 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			104 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 13\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$			250 ns
I_{RM}			10.2	A
Q_{RM}			0.9	μC

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ISO TO-247 (IXFJ) OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.087	.100	2.21	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.085	1.91	2.16
b4	.115	.126	2.92	3.20
c	.023	.033	0.58	0.84
D	.820	.840	20.83	21.34
E	.620	.635	15.75	16.13
E2	.175	.195	4.44	4.95
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.160	.177	4.06	4.50
Q	.220	.240	5.59	6.10
R	.520	.540	13.21	13.72
S	.242 BSC		6.15 BSC	
T	.355	.375	9.02	9.53
U	.345	.370	8.76	9.40
ϕP	.140	.144	3.55	3.66
W	.000	.004	0.00	0.10

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

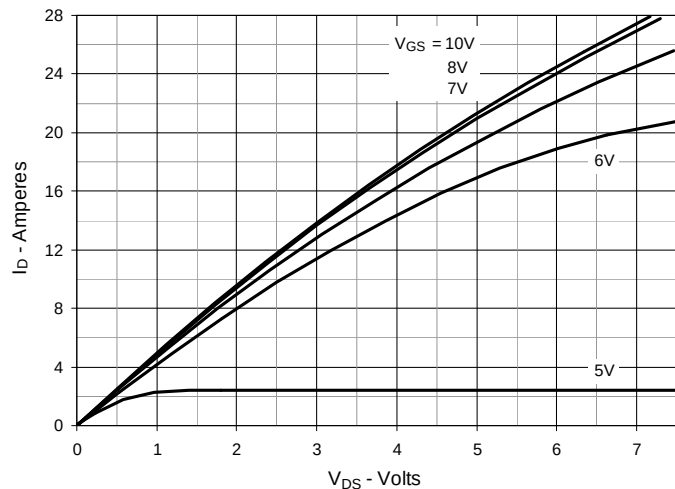
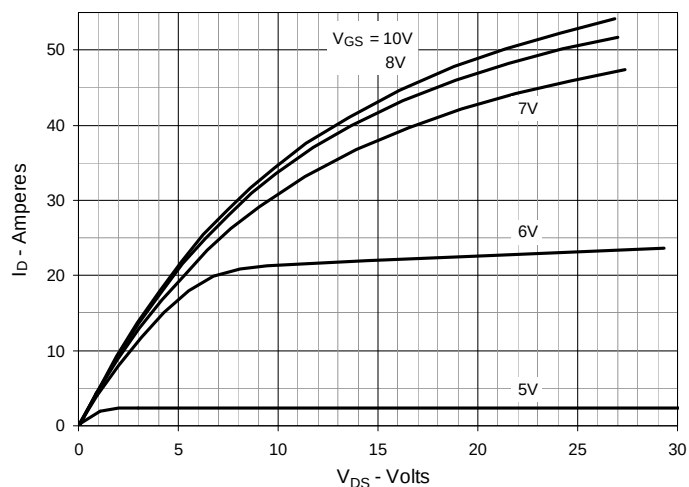
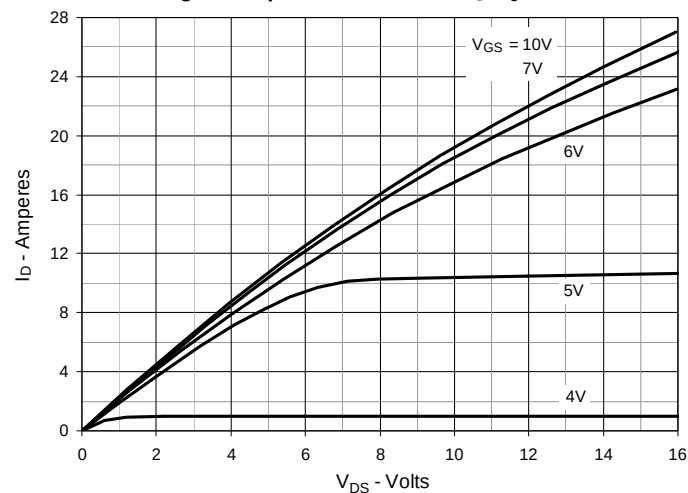
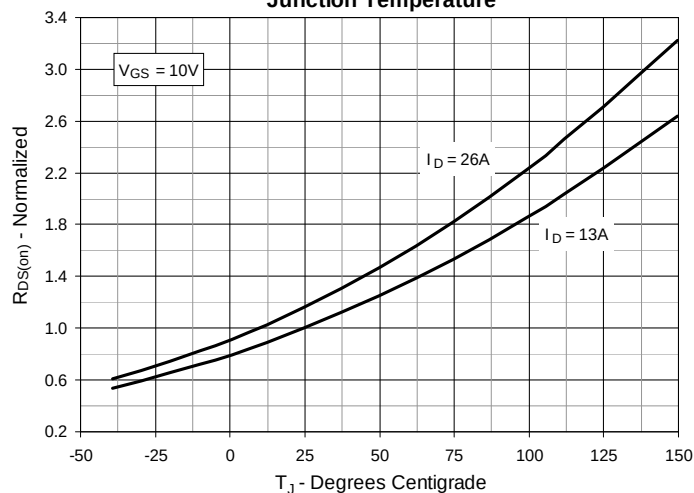
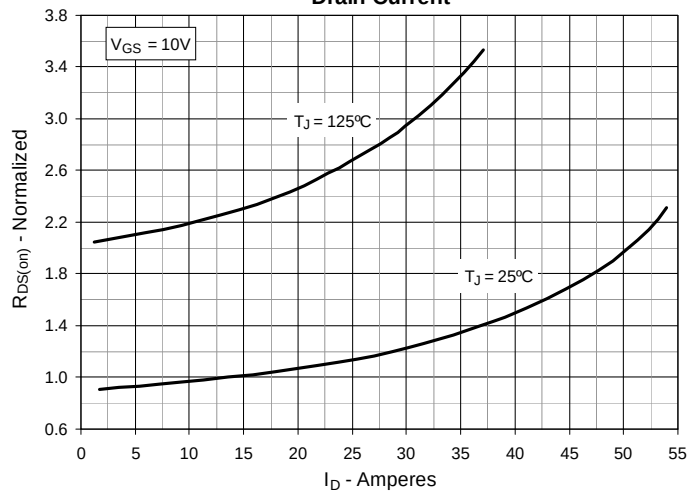
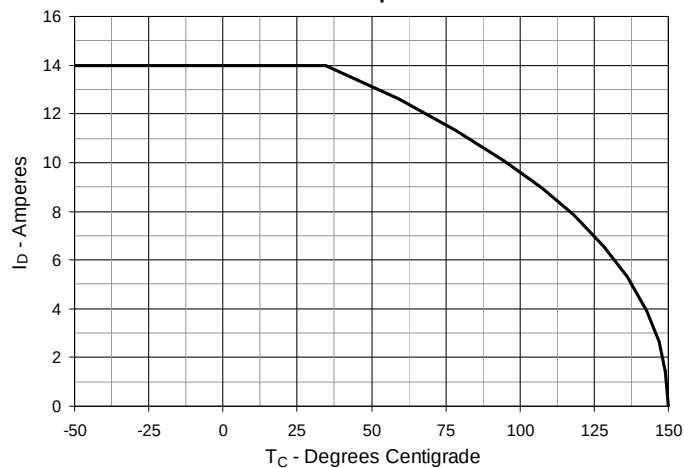
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 13\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 13\text{A}$ Value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature


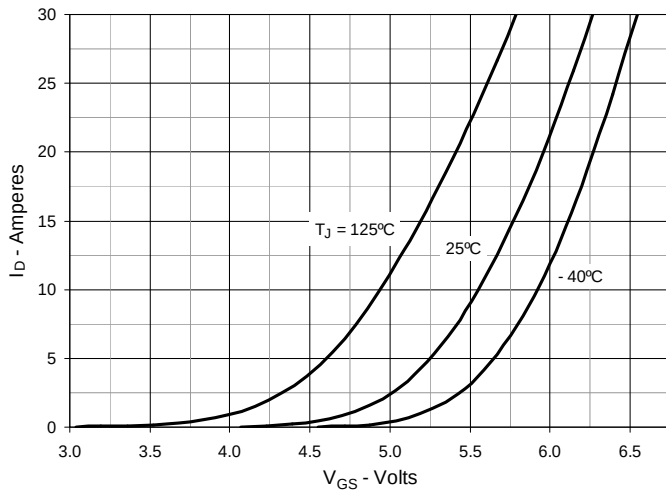
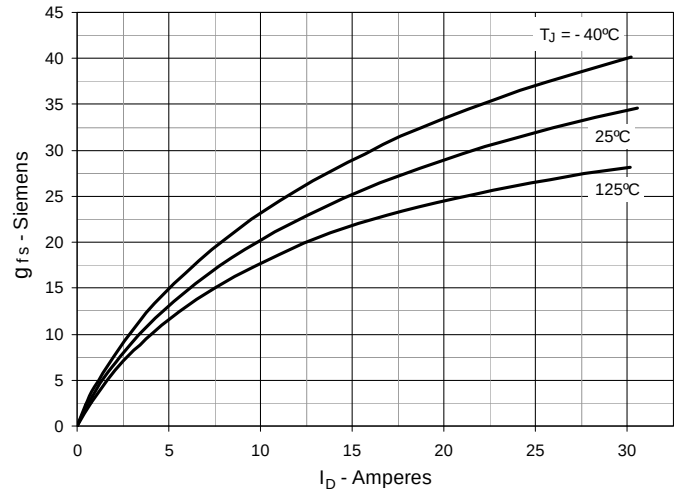
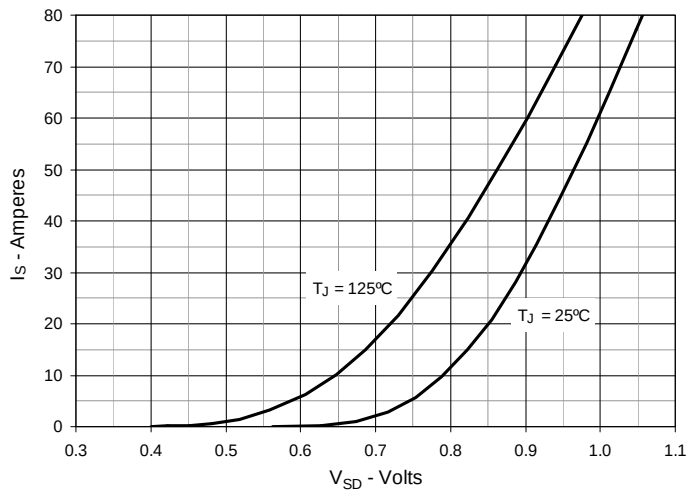
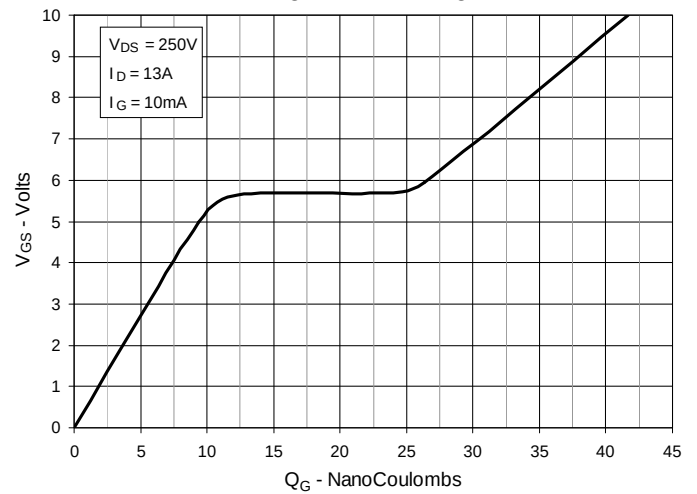
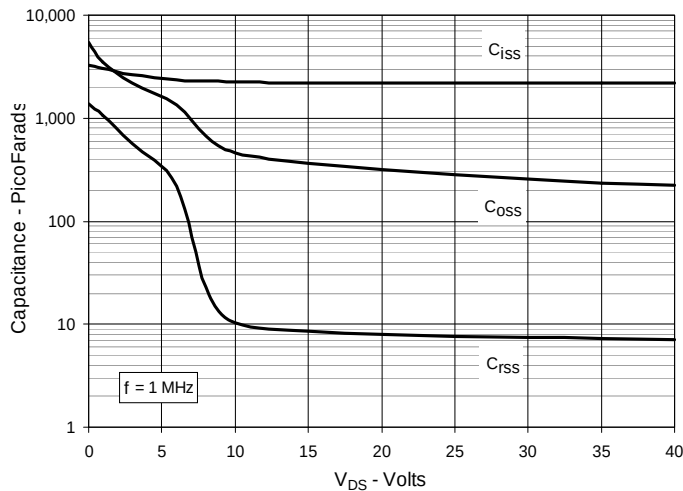
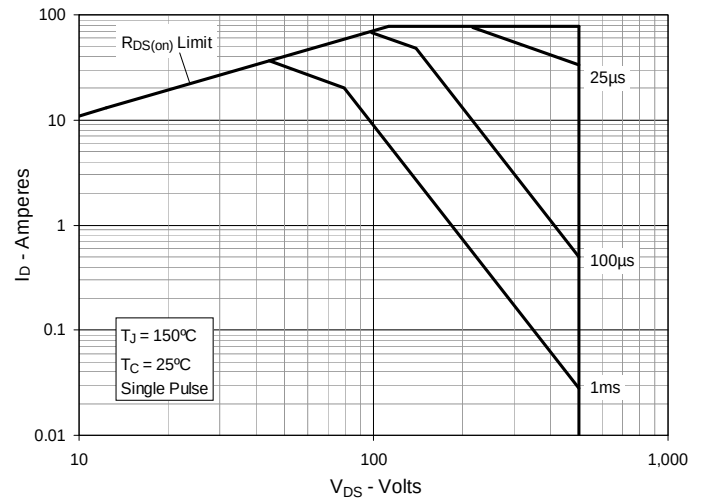
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Maximum Transient Thermal Impedance

